



ATTORNEY DOCKET NO.: LOTFI 22-2

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Ashraf W. Lotfi, *et al.*
Serial No.: 09/448,856
Filed: November 23, 1999
Title: SiC NMOSFET FOR USE AS A POWER SWITCH AND
A METHOD OF MANUFACTURING THE SAME
Group: 2811
Examiner: Ori Nadav

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner for Patents, Alexandria, VA 22313, on	
8-29-03	(Date)
Elizabeth Schumacher	
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Elizabeth Schumacher	
(Signature of the person signing the certificate)	

Sir:

REQUEST FOR RECONSIDERATION UNDER 37 C.F.R. § 1.111

In response to the Examiner's Action mailed May 30, 2003, please reconsider the above-identified application for the following reasons.

IN THE CLAIMS:

Claims 1-43 were previously canceled without prejudice or disclaimer.

44. (Previously Presented) A semiconductor device, comprising:
- a lateral metal-oxide semiconductor field effect transistor (MOSFET), including:
- a silicon carbide tub located within a trench formed in a conductive substrate;

2811
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for
Recon.
9/11/03
PATENT
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TC 2600 MAIL ROOM
Adm th